

## REMARKS/ARGUMENTS

Claim 1 has been amended and now calls for the following combination:

A DC-DC converter comprising:  
a synchronous semiconductor device; and  
a control semiconductor device;  
wherein at least one of said semiconductor devices includes:  
a semiconductor body of a first conductivity which includes a channel region of a second conductivity and a major surface;  
an active region formed in said semiconductor body, said active region including a trench less than 0.5 microns wide extending through said channel region and a gate structure disposed in said trench which includes a gate oxide layer disposed at least on said sidewalls of said trench and a gate electrode disposed adjacent said gate oxide layer, conductive regions of said first conductivity adjacent said trench in said channel region; and a metallic contact in contact with said conductive regions; and  
a termination structure, said termination structure including,  
a termination trench having a slanted sidewall formed in said semiconductor body, and a grown field oxide layer formed in said termination trench below said major surface, a polysilicon field plate formed over said field oxide layer, and a low temperature oxide body over said polysilicon field plate, wherein said field oxide layer is thicker than said gate oxide layer, wherein said metallic contact extends over said low temperature oxide body, and wherein said semiconductor body of said first conductivity extends from said trench to the bottom of said termination trench.

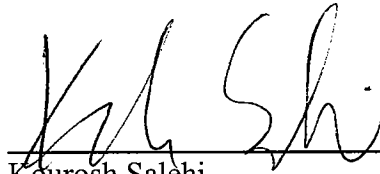
The following features are not shown by Zeng, nor suggested by other art of record in combination with other limitations set forth in claim 1:

- A) a termination trench having a slanted sidewall;
- B) a grown field oxide in the termination trench;
- C) a low temperature oxide body extending over a polysilicon field plate; wherein a metallic contact which is in contact with the conductive regions in the channel region extends over the low temperature oxide body; and
- D) a semiconductor body of a first conductivity which extends between the trench and the termination trench.

For at least the distinguishing features set forth above, claim 1 should be deemed allowable over the art of record. Such action is earnestly solicited.

THIS CORRESPONDENCE IS BEING  
SUBMITTED ELECTRONICALLY  
THROUGH THE PATENT AND  
TRADEMARK OFFICE EFS FILING  
SYSTEM ON December 18, 2006.

Respectfully submitted,

A handwritten signature in black ink, appearing to read 'K. Salehi', is written over a horizontal line.

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